

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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SD1536-03

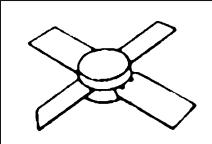
RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

Features

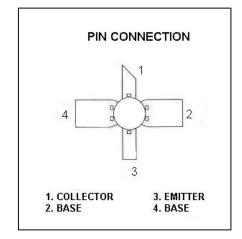
- 1025 1150 MHz
- 50 VOLTS
- P_{OUT} = 90 W
- G_P = 8.4 dB MINIMUM
- INPUT MATCHED
- COMMON BASE CONFIGURATION

DESCRIPTION:

The SD1536-03 is a gold metallized silicon NPN power transistor designed for applications requiring high peak power and low duty cycles such as IFF, DME and TACAN. Internal Impedance matching provides improved broadband performance.



.280 4LSL (M115) hermetically sealed



ABSOLUTE MAXIMUM RATINGS (T_{CASE} = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector – Base Voltage	65	V
V _{CES}	Collector – Emitter Voltage	65	V
V _{EBO}	Emitter – Base Voltage	3.5	V
Ic	Device Current	10	Α
P _{DISS}	Power Dissipation	292	W
TJ	Juction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

THERMAL DATA

R _{TH(J-C)}	Junction-Case Thermal Resistance	0.60	°C/W
111(3-0)		0.00	•,



SD1536-03

ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

Symbol		Test Conditions		Value		Unit
		rest Conditions	Min.	Тур.	Max.	Unit
BV _{CBO}	I _C = 10 mA	I _E = 0 mA	65			V
BV _{CER}	I _C = 25 mA	R_{BE} =10 Ω	65			V
BV _{EBO}	I _E = 1 mA	$I_C = 0 \text{ mA}$	3.5			V
I _{CES}	V _{CE} = 50 V	I _E = 0 mA			10	mA
h _{FE}	V _{CE} = 5 V	$I_C = 100 \text{ mA}$	5			

DYNAMIC

Cymbol	Symbol Test Conditions		Value			Unit	
Syllibol			Min.	Тур.	Max.	Offic	
P _{out}	f = 1025 - 1150MHz	P _{IN} = 13.0 W	V _{CE} = 50 V	90			W
G _P	f = 1025 - 1150MHz	P _{IN} = 13.0 W	V _{CE} = 50 V	8.4			dB

Conditions: Pulse Width = 10 μ Sec, Duty Cycle = 1%

This device is suitable for use under other pulse width/duty cycle conditions.

Please contact the factory for specific applications assistance.

IMPEDANCE DATA

FREQ	$Z_IN(\Omega)$	$Z_{CL}(\Omega)$
960 MHz	2.5 + j13.0	4.6 – j5.5
1030 MHz	5.2 + j15.0	5.0 – j5.5
1090 MHz	16.3 + j15.0	4.8 – j5.5
1150 MHz	14.7 + j2.5	4.7 – j7.0
1215 MHz	7.6 + j0.5	4.7 – j5.0

P_{IN}=13W V_{CE} = 50 V





PACKAGE MECHANICAL DATA

